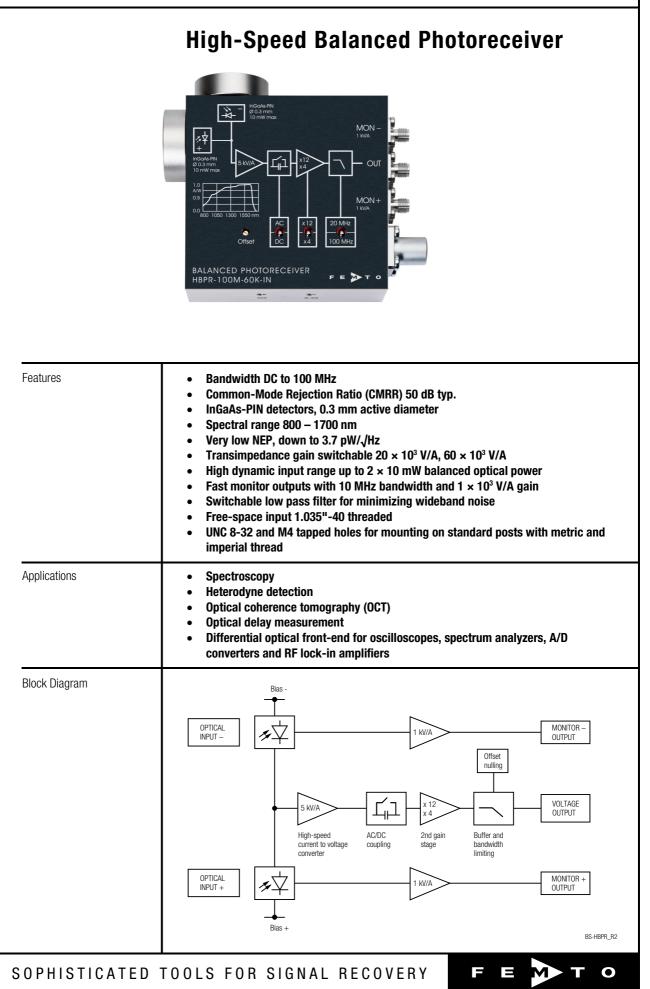
Datasheet



High-Speed Balanced Photoreceiver

Intended Use	The HBPR-100M-60K-IN-FST photoreceiver consists of a combination of two anti-parallel connected photodiodes with a subsequent low-noise transimpedance amplifier. It is designed for fast conversion of the tiny difference of two optical signals into an equivalent output voltage. Operation is mostly self-explanatory. If in doubt, consult this document or contact support@femto.de. For safe operation, please refer to the damage thresholds specified in the "Absolute Maximum Ratings", "Temperature Range" and "Power Supply" sections of this document. The operating environment must be free of smoke, dust, grease, oil, condensing moisture, and other contaminants that could affect the operation or performance.		
Application Notes	The damage threshold of 12 mW for each photodiode mentioned in the "Absolute Maximum Ratings" section applies to reasonably homogeneous illumination of the photodiodes. Extreme focusing of the light beam can lead to damage to the photodiodes, even at significantly lower light power.		
	To achieve optimum performance, it is recommended that the CW light intensity at both inputs be well balanced. The monitor outputs can be used for continuous balance control. For setups with arbitrarily varying CW offset, the photoreceiver's AC mode can be helpful. Using AC mode increases the CW offset range to 275 μ W (@ 1550 nm), regardless of the gain setting.		
Available Version	HBPR-100M-60K-IN-FST	1.035"-40 threaded flanges with internally threaded coupler rings mounted (outer dia. 30 mm), for free space applications, compatible with many optical standard accessories	
Related Models	Various free space or fiber coupled HBPR models, with bandwidth up to 500 MHz, in the spectral range from 320 nm to 1700 nm are available.		
Si Versions	Fiber-coupled with fix/permanent FC fiber connectors		
	HBPR-100M-60K-SI-FC	Si-PIN \varnothing 0.8 mm, DC – 100 MHz, 320 – 1000 nm, CMRR 50 dB, gain 2.0 × 10 ⁴ / 6.0 × 10 ⁴ V/A switchable	
	HBPR-200M-30K-SI-FC	Si-PIN \oslash 0.8 mm, DC – 200 MHz, 320 – 1000 nm, CMRR 45 dB, gain 1.0 \times 10 ⁴ / 3.0 \times 10 ⁴ V/A switchable	
	HBPR-500M-10K-SI-FC	Si-PIN Ø 0.4 mm, DC – 500 MHz, 320 – 1000 nm, CMRR 40 dB, gain 5.0 \times 10 3 / 10.0 \times 10 3 V/A switchable	
	Free space versions with 1.035"-40 threaded flanges		
	HBPR-100M-60K-SI-FST	Si-PIN \varnothing 0.8 mm, DC – 100 MHz, 320 – 1000 nm, CMRR 50 dB, gain 2.0 × 10 ⁴ / 6.0 × 10 ⁴ V/A switchable	
	HBPR-200M-30K-SI-FST	Si-PIN \oslash 0.8 mm, DC – 200 MHz, 320 – 1000 nm, CMRR 45 dB, gain 1.0 × 10 ⁴ / 3.0 × 10 ⁴ V/A switchable	
	HBPR-500M-10K-SI-FST	Si-PIN Ø 0.4 mm, DC – 500 MHz, 320 – 1000 nm, CMRR 40 dB, gain 5.0 \times 10 3 / 10.0 \times 10 3 V/A switchable	
	TOOLS FOR SIGNA		

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High-Speed Balanced Photoreceiver

Fiber-coupled with fix/permanent HBPR-100M-60K-IN-FC HBPR-200M-30K-IN-FC	FC fiber connectors (ball lense coupled) InGaAs-PIN \oslash 0.08 mm, DC – 100 MHz, 900 – 1700 nm, CMRR 55 dB, gain 2.0 × 10 ⁴ / 6.0 × 10 ⁴ V/A switchable	
	CMRR 55 dB, gain 2.0 \times 10 ⁴ / 6.0 \times 10 ⁴ V/A switchable	
HBPR-200M-30K-IN-FC	$\ln C_0 \Lambda_0 D[N] \propto 0.00 \text{ mm} DC = 0.00 \text{ MU}_{7} 0.00 = 1700 \text{ mm}$	
	InGaAs-PIN \oslash 0.08 mm, DC – 200 MHz, 900 – 1700 nm, CMRR 50 dB, gain 1.0 × 10 ⁴ / 3.0 × 10 ⁴ V/A switchable	
HBPR-500M-10K-IN-FC	InGaAs-PIN \oslash 0.08 mm, DC – 500 MHz, 900 – 1700 nm, CMRR 45 dB, gain 5.0 × 10 ³ / 10.0 × 10 ³ V/A switchable	
Free space versions with 1.035"-40 threaded flanges		
HBPR-200M-30K-IN-FST	InGaAs-PIN \oslash 0.3 mm, DC – 200 MHz, 800 – 1700 nm, CMRR 45 dB, gain 1.0 × 10 ⁴ / 3.0 × 10 ⁴ V/A switchable	
HBPR-450M-10K-IN-FST	InGaAs-PIN \oslash 0.3 mm, DC – 450 MHz, 800 – 1700 nm, CMRR 35 dB, gain 5.0 × 10 ³ / 10.0 × 10 ³ V/A switchable	
PS-15-25-L	Power Supply Input: 100 – 240 VAC Output: ±15 VDC	
Test conditions	$\label{eq:VS} \begin{array}{l} V_{S}=\pm15~V,~T_{\text{A}}=25~^{\circ}\text{C},~output~load~impedance~50~\Omega,\\ warm-up~20~minutes~(min.~10~minutes~recommended),\\ monitor~outputs~terminated~with~1~M\Omega \end{array}$	
Transimpedance gain	20 × 10 ³ V/A (@ 2 nd gain ×4, 50 Ω load) 60 × 10 ³ V/A (@ 2 nd gain ×12, 50 Ω load)	
Gain accuracy	±1 % electrical	
Conversion gain	19 × 10 ³ V/W typ. (@ 2 nd gain ×4, 1550 nm, 50 Ω load) 57 × 10 ³ V/W typ. (@ 2 nd gain ×12, 1550 nm, 50 Ω load)	
Common mode rejection ratio (CMRR)	50 dB typ. (f $\leq 100 \text{ MHz}$)	
Lower cut-off frequency Upper cut-off frequency (–3 dB)	DC / 10 Hz, switchable 100 MHz / 20 MHz, switchable	
Rise/fall time (10 % – 90 %)	3.4 ns 17.5 ns (@ bandwidth set to 20 MHz)	
Noise equivalent power (NEP)	minimum 3.7 pW/,/Hz (@ 1550 nm) 4.3 pW/,/Hz (@ 1550 nm, 20 MHz) 7.1 pW/,/Hz (@ 1550 nm, 50 MHz) 12.0 pW/,/Hz (@ 1550 nm, 100 MHz)	
Maximum differential CW power (for linear amplification)	53 μW (@ 2 nd gain ×4, DC-coupled, 1550 nm) 18 μW (@ 2 nd gain ×12, DC-coupled, 1550 nm) 275 μW (@ AC-coupled, 1550 nm)	
Max. optical CW balanced power (common mode power)	10 mW (on each photodiode, @ 1550 nm)	
Monitor optical saturation power (limited by linear amplification)	10.5 mW (@ 1550 nm)	
Detector type Active area Spectral range Sensitivity	InGaAs-PIN photodiode Ø 300 μm 800 – 1700 nm 0.95 A/W typ. (@ 1550 nm)	
	HBPR-200M-30K-IN-FST HBPR-450M-10K-IN-FST PS-15-25-L Test conditions Transimpedance gain Gain accuracy Conversion gain Common mode rejection ratio (CMRR) Lower cut-off frequency Upper cut-off frequency (-3 dB) Rise/fall time (10 % – 90 %) Noise equivalent power (NEP) Maximum differential CW power (for linear amplification) Max. optical CW balanced power (monitor optical saturation power (limited by linear amplification) Detector type Active area Spectral range	

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High-Speed Balanced Photoreceiver

Output voltage range Max. output voltage	$\pm 1.0 \text{ V}$ (@ 50 Ω load) for linear operation and low harmonic distortion
Offset voltage compensation Output impedance Slew rate Max. output current Output reflection S22 Output noise (typ.)	$\pm 2.0 V (@ 50 Ω load)$ $\pm 100 mV typ., adjustable by offset potentiometer$ 50 Ω (terminate with 50 Ω load) 2000 V/µs 70 mA -30 dB @ < 100 MHz -20 dB @ < 800 MHz $2.2 mV_{RMS} (15 mV peak-peak) (@ 2nd gain ×4)$ 6.2 mV RMS (41 mV peak-peak) (@ 2nd gain ×12) 0.5 mV RMS (3.1 mV peak-peak) (@ 2nd gain ×4, BW 20 MHz) 1.3 mV RMS (8.8 mV peak-peak) (@ 2nd gain ×12, BW 20 MHz) (@ 50 Ω load, no signal on detectors, measurement bandwidth 2 GHz)
Gain Voltage range Output impedance Max. output current Bandwidth Output noise	1 × 10 ³ V/A (@ ≥ 100 kΩ load) 0 +10 V (@ ≥ 100 kΩ load) 50 Ω (terminate with ≥ 100 kΩ load) 30 mA typ. DC – 10 MHz 0.6 mV RMS (4 mV peak-peak) (@ 100 kΩ load, no signal on detectors, measurement bandwidth 200 MHz)
Supply voltage Supply current	± 15 V (± 14.5 V ± 16.5 V) -90 / +120 mA typ. (depends on operating conditions, recommended power supply capability min. ± 200 mA)
Material FST flange Material FST coupler ring	1.4305 stainless steel, nickel-plated 1.4305 stainless steel, glass bead blasted
Weight Material	410 g (0.9 lbs) including coupler rings AIMg3Mn, nickel-plated
Storage temperature Operating temperature	-40 °C +85 °C 0 °C +60 °C
Optical input power (CW) Power supply voltage	12 mW (on each photodiode) ±20 V
Inputs	1.035"-40 threaded flanges for free space applications and for use with various types of optical standard accessories
Power supply	SMA jacks (female) LEMO [®] series 1S, 3-pin fixed socket (mating plug type: FFA.1S.303.CLAC52)
	PIN 2 O PIN 1 Pin 1: +15 V -Vs -Vs Pin 2: -15 V Pin 3: GND
HBPR-100M-60K-IN-FST, 2 \times t 3 \times adapter SMA (male) to BNC	threaded coupler ring, Lemo [®] 3-pin connector, C (female), datasheet
-	Output reflection S22 Output noise (typ.) Gain Voltage range Output impedance Max. output current Bandwidth Output noise Supply voltage Supply voltage Supply voltage Supply current Material FST flange Material FST coupler ring Weight Material Storage temperature Optical input power (CW) Power supply voltage Inputs Outputs Power supply Power supply HBPR-100M-60K-IN-FST, 2 × t

